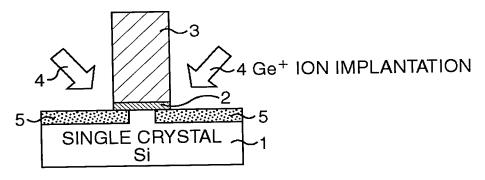
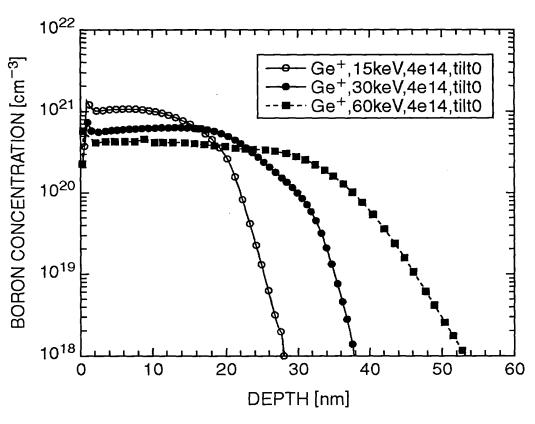
FIG. 1



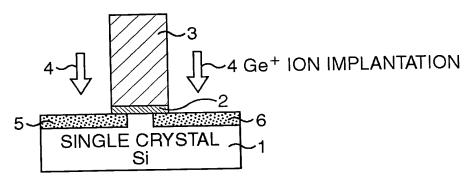
PARTS UNDER GATE ELECTRODE ALSO AMORPHOUSIZED BY OBLIQUE AMORPHOUSIZING IMPLANTATION (IMPURITIES IN THESE PARTS ACTIVATED)

FIG. 2



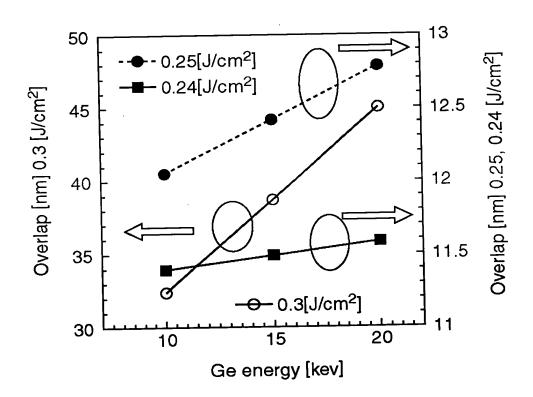
SECONDARY ION MASS SPECTROMETRY

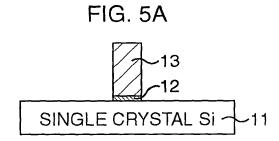
FIG. 3

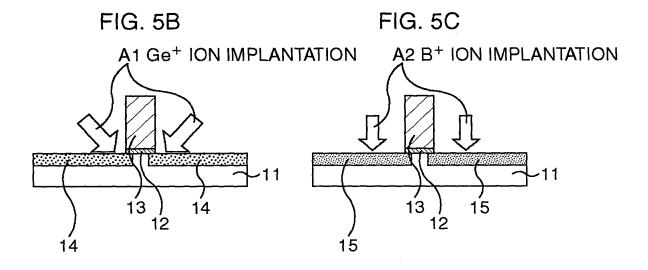


SOURCE/DRAINS HAVING PARTS UNDER GATE ELECTRODE ALSO AMORPHOUSIZED FORMED BY CONTROLLING ION IMPLANTATION CONDITION AND LASER IRRADIATION CONDITION (IMPURITIES IN THESE PARTS ACTIVATED)

FIG. 4







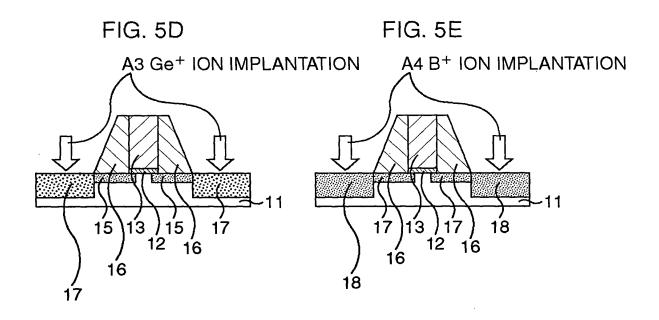


FIG. 6A

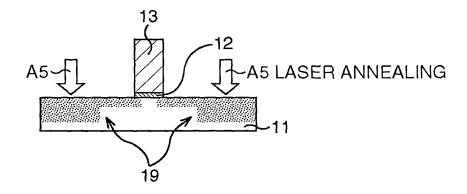


FIG. 6B

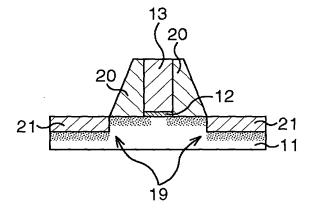


FIG. 6C

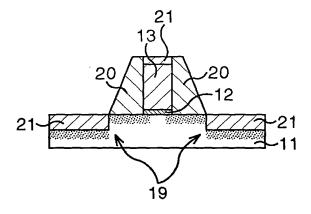


FIG. 7A

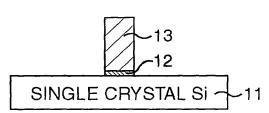


FIG. 7B

Til+30

Ge+ ION IMPLANTATION

13

Til+30

Ge+ ION IMPLANTATION

31a

31a

FIG. 7C

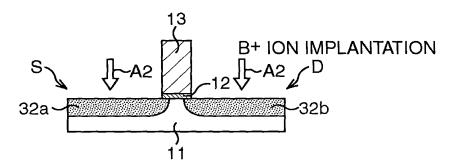


FIG. 7D

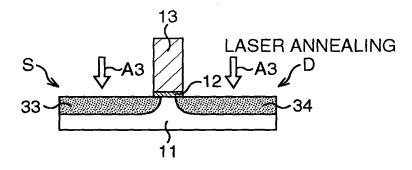


FIG. 8A

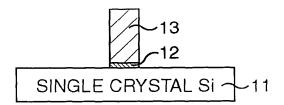


FIG. 8B

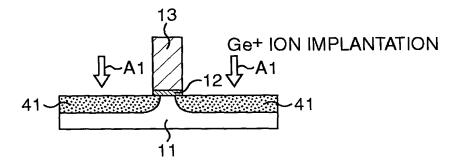


FIG. 8C

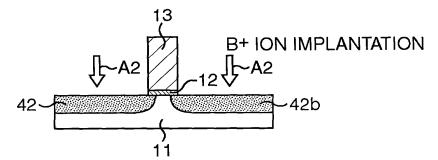


FIG. 8D

